

H5N3007FN

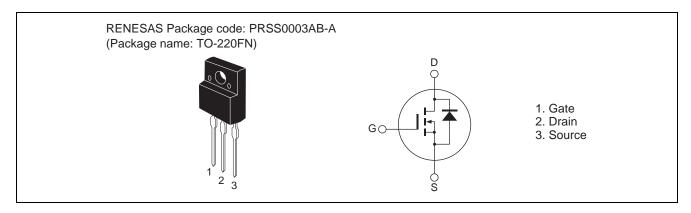
Silicon N Channel MOS FET High Speed Power Switching

REJ03G1860-0100 Rev.1.00 Nov 09, 2009

Features

- Low on-resistance
- Low leakage current
- High speed switching
- Built-in fast recovery diode

Outline



Absolute Maximum Ratings

 $(Ta = 25^{\circ}C)$

Item	Symbol	Ratings	Unit
Drain to source voltage	V_{DSS}	300	V
Gate to source voltage	V _{GSS}	±30	V
Drain current	I _D	15	Α
Drain peak current	I _{D (pulse)} Note1	60	Α
Body-drain diode reverse drain current	I _{DR}	15	Α
Body-drain diode reverse drain peak current	I _{DR (pulse)} Note1	60	Α
Avalanche current	I _{AP} Note3	15	Α
Avalanche energy	E _{AR} Note3	13.5	mJ
Channel to case thermal impedance	θch-c	3.57	°C/W
Channel dissipation	Pch Note2	35	W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	-55 to +150	°C

Notes: 1. PW \leq 10 μ s, duty cycle \leq 1%

2. Value at Tc = 25°C

3. STch = 25° C, Tch $\leq 150^{\circ}$ C

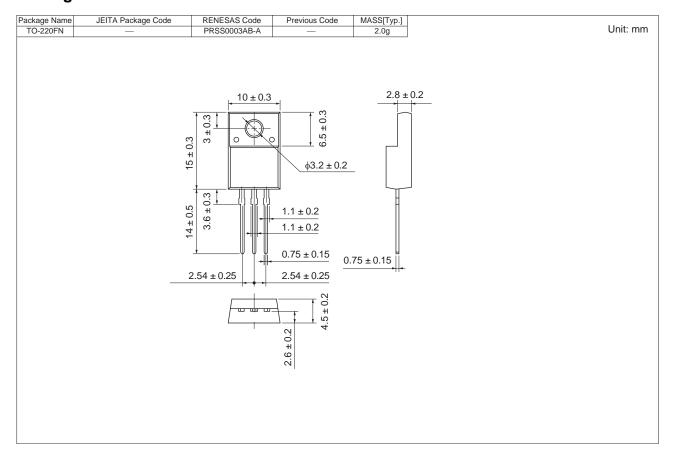
Electrical Characteristics

 $(Ta = 25^{\circ}C)$

Item	Symbol	Min	Тур	Max	Unit	Test conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	300	_	_	V	$I_D = 10 \text{ mA}, V_{GS} = 0$
Zero gate voltage drain current	I _{DSS}	_	_	10	μΑ	$V_{DS} = 300 \text{ V}, V_{GS} = 0$
Gate to source leak current	I _{GSS}		_	±0.1	μΑ	$V_{GS} = \pm 30 \text{ V}, V_{DS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	1.5	_	4.0	V	$V_{DS} = 10 \text{ V}, I_{D} = 1 \text{ mA}$
Forward transfer admittance	yfs	9	15	_	S	$I_D = 7.5 \text{ A}, V_{DS} = 10 \text{ V}^{\text{Note4}}$
Static drain to source on state	R _{DS(on)}	_	0.12	0.16	Ω	$I_D = 7.5 \text{ A}, V_{GS} = 10 \text{ V}^{\text{Note4}}$
resistance						
Input capacitance	Ciss		2180		pF	V _{DS} = 25 V
Output capacitance	Coss	_	275	_	pF	$V_{GS} = 0$
Reverse transfer capacitance	Crss	_	77	_	pF	f = 1 MHz
Turn-on delay time	t _{d(on)}	_	35	_	ns	I _D = 7.5 A
Rise time	t _r	_	50	_	ns	V _{GS} = 10 V
Turn-off delay time	t _{d(off)}	_	160	_	ns	$R_L = 20 \Omega$
Fall time	t _f	_	40	_	ns	$Rg = 10 \Omega$
Total gate charge	Qg	_	81	_	nC	V _{DD} = 240 V
Gate to source charge	Qgs	_	10	_	nC	V _{GS} = 10 V
Gate to drain charge	Qgd	_	38	_	nC	I _D = 15 A
Body-drain diode forward voltage	V_{DF}	_	0.85	1.30	V	$I_F = 15 \text{ A}, V_{GS} = 0^{\text{Note4}}$
Body-drain diode reverse recovery time	t _{rr}	_	110	_	ns	$I_F = 15 \text{ A}, V_{GS} = 0$ $di_F/dt = 100 \text{ A}/\mu\text{s}$

Notes: 4. Pulse test

Package Dimensions



Ordering Information

Part No.	Quantity	Shipping Container
H5N3007FN-E	1050 pcs	Box (Tube)

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